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SEMICONDUCTOR



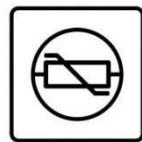
ESD



TVS



TSS



MOV



GDT



PLED


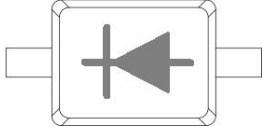
BZT52B2V4S-BZT52B39S

Product specification

FEATURES

- Planar Die Construction
- General Purpose, Medium Current
- Ideally Suited for Automated Assembly Processes
- Available in Lead Free Version

Reference News

PACKAGE OUTLINE	PIN CONFIGURATION
	
SOD-323	

Maximum Ratings (Ta=25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Forward Voltage (Note 2) @ I _F = 10mA	V _F	0.9	V
Power Dissipation(Note 1)	P _d	200	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	625	°C/W
Operation Junction and Storage Temperature Range	T _J , T _{stg}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS

 T_a=25°C unless otherwise specified

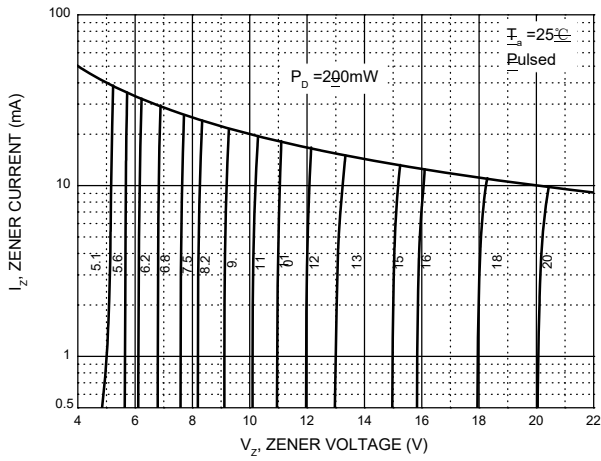
Type Number	Type Code	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current		Typical Temperature Coefficient @I _{ZTC}		Test Current I _{ZTC}
		V _{Z@I_{ZT}}			I _{ZT}	Z _{ZT@I_{ZT}}	Z _{ZK@I_{ZK}}	I _{ZK}	I _R	V _R	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	μA	V	Min	Max	
BZT52B2V4S	2WX	2.4	2.35	2.45	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52B2V7S	2W1	2.7	2.65	2.75	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52B3V0S	2W2	3.0	2.94	3.06	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52B3V3S	2W3	3.3	3.23	3.37	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52B3V6S	2W4	3.6	3.53	3.67	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52B3V9S	2W5	3.9	3.82	3.98	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V3S	2W6	4.3	4.21	4.39	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V7S	2W7	4.7	4.61	4.79	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52B5V1S	2W8	5.1	5.00	5.20	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52B5V6S	2W9	5.6	5.49	5.71	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52B6V2S	2WA	6.2	6.08	6.32	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52B6V8S	2WB	6.8	6.66	6.94	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52B7V5S	2WC	7.5	7.35	7.65	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52B8V2S	2WD	8.2	8.04	8.36	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52B9V1S	2WE	9.1	8.92	9.28	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52B10S	2WF	10	9.80	10.20	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52B11S	2WG	11	10.78	11.22	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52B12S	2WH	12	11.76	12.24	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52B13S	2WI	13	12.74	13.26	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52B15S	2WJ	15	14.70	15.30	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52B16S	2WK	16	15.68	16.32	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52B18S	2WL	18	17.64	18.36	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52B20S	2WM	20	19.60	20.40	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52B22S	2WN	22	21.56	22.44	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52B24S	2WO	24	23.52	24.48	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52B27S	2WP	27	26.46	27.54	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52B30S	2WQ	30	29.40	30.60	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52B33S	2WR	33	32.34	33.66	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52B36S	2WS	36	35.28	36.72	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52B39S	2WT	39	38.22	39.78	2	130	350	0.5	0.1	27.3	33.4	41.2	2

 Notes: 1. Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²

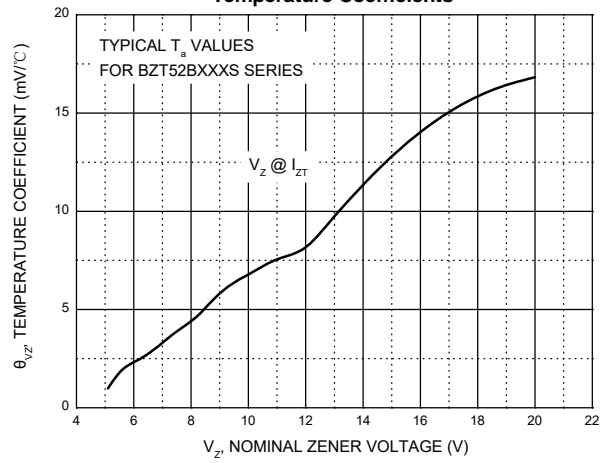
2. Short duration test pulse used to minimize self-heating effect.

3. f = 1kHz.

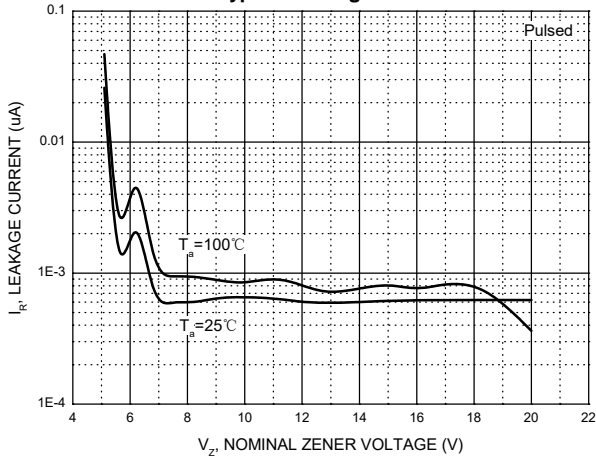
Zener Characteristics (V_z 5.1V to 20 V)



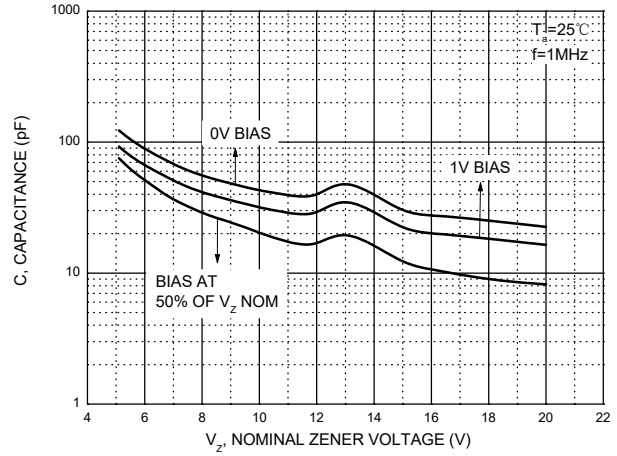
Temperature Coefficients



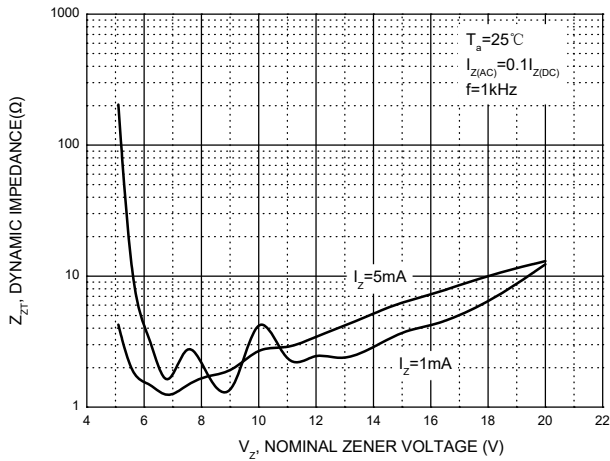
Typical Leakage Current



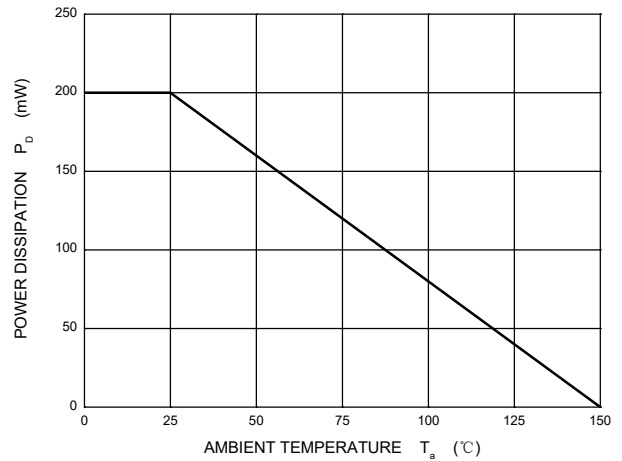
Typical Capacitance



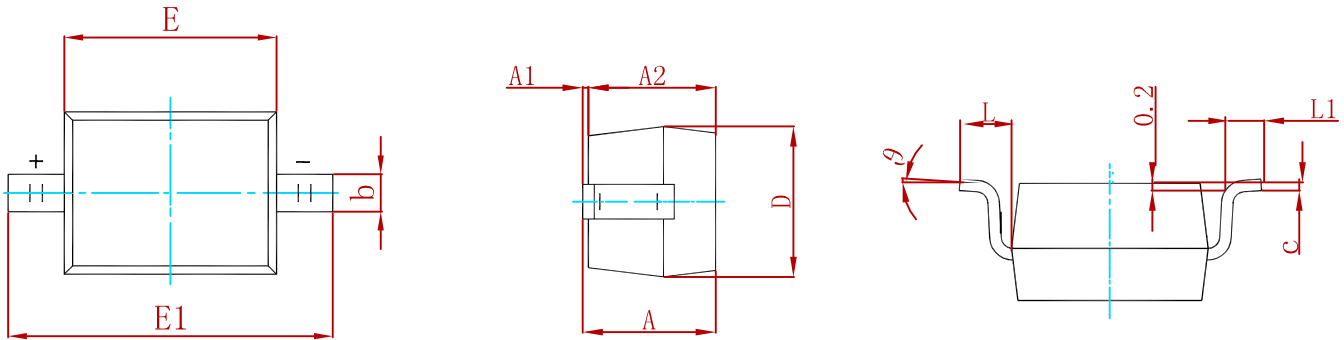
Effect of Zener Voltage on Zener Impedance



Power Derating Curve

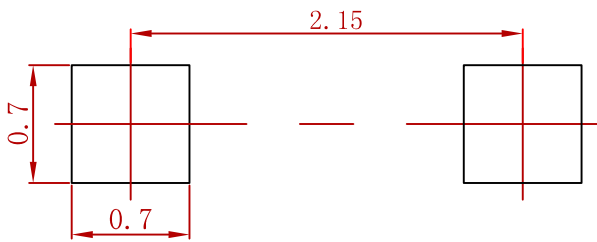


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BZT52B2V4S-BZT52B39S	SOD-323	3000

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